











SN74LVC1G32

SCES219V - APRIL 1999-REVISED AUGUST 2015

SN74LVC1G32 Single 2-Input Positive-OR Gate

Features

- Available in the Ultra-Small 0.64 mm² Package (DPW) with 0.5-mm Pitch
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5-V
- Supports Down Translation to V_{CC}
- Max t_{od} of 3.6 ns at 3.3-V
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3-V
- Ioff Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- **AV Receiver**
- Blu-ray Player and Home Theater
- Digital Picture Frame (DPF)
- Embedded PC
- IP Phone: Wireless
- High-Speed Data Acquisition and Generation
- Motor Control: High-Voltage
- Optical Networking: Video Over Fiber and EPON
- Personal Navigation Device (GPS)
- Portable Media Player
- Private Branch Exchange (PBX)
- Server PSU
- SSD: Internal and External
- TV: LCD/Digital and High-Definition (HDTV)
- Telecom Shelter: Power Distribution Unit (PDU), Power Monitoring Unit (PMU), Wireless Battery Monitoring, Remote Electrical Tilt Unit (RET), Remote Radio Unit (RRU), Tower Mounted Amplifier (TMA)
- Video Conferencing: IP-Based HD
- Vector Signal Analyzer and Generator
- WiMAX and Wireless Infrastructure Equipment
- Wireless Headset, Keyboard, Mouse, and Repeater

3 Description

This single 2-input positive-OR gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G32 device performs the Boolean function $Y = A + B \text{ or } Y = \overline{A \cdot B}$ in positive logic.

The CMOS device has high output drive while maintaining low static power dissipation over a broad V_{CC} operating range.

The SN74LVC1G32 device is available in a variety of packages, including the ultra-small DPW package with a body size of 0.8×0.8 mm.

Device Information⁽¹⁾

DEVICE NAME	PACKAGE (PINS)	BODY SIZE
SN74LVC1G32DBV	SOT-23 (5)	2.90 mm × 2.80 mm
SN74LVC1G32DCK	SC70 (5)	2.00mm × 2.10 mm
SN74LVC1G32DRY	SON (6)	1.45 mm × 1.00 mm
SN74LVC1G32DSF	SON (6)	1.00 mm × 1.00 mm
SN74LVC1G32DPW	X2SON (4)	0.80 mm × 0.80 mm
SN74LVC1G32DRL	SOT (5)	1.60 mm × 1.60 mm
SN74LVC1G32YZP	DSBGA (5)	1.38 mm × 0.88 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.





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Changes from Revision R (June 2013) to Revision S

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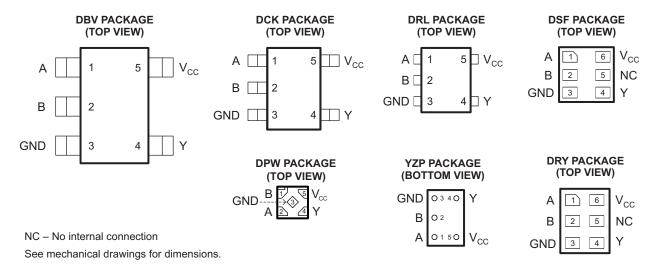




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5 Pin Configuration and Functions



Pin Functions

	PI	N		
NAME	DBV, DCK, DRL, YZP	DRY, DSF	DPW	DESCRIPTION
Α	1	1	2	Input
В	2	2	1	Input
GND	3	3	3	Ground
Υ	4	4	4	Output
VCC	5	6	5	Power pin
NC	_	5	_	Not connected



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range ⁽²⁾			6.5	V
Vo	Voltage range applied to any output in the high-i	-0.5	6.5	V	
Vo	Voltage range applied to any output in the high or low state (2)(3)			V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND		±100	mA	
TJ	Junction temperature	-65	150	°C	
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

	PARAMETER	DEFINITION	VAUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	±2000	
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the Recommended Operating Conditions table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT			
.,	Complementaria	Operating	1.65	5.5	V			
V_{CC}	Supply voltage	Data retention only	1.5		V			
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}					
\	High level input valtage	V _{CC} = 2.3 V to 2.7 V	1.7					
V_{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V			
		$V_{CC} = 4.5 \text{ V}$ to 5.5 V						
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}				
.,	Law Israel Court wells as	V _{CC} = 2.3 V to 2.7 V		0.7				
V_{IL}	Low-level input voltage $V_{CC} = 3 \text{ V to } 3.6 \text{ V}$			0.8	V			
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}				
VI	Input voltage		0	5.5	V			
Vo	Output voltage		0	V _{CC}	V			
		V _{CC} = 1.65 V		-4				
		V _{CC} = 2.3 V		-8				
I _{OH}	High-level output current	V 0 V		-16	mA			
		V _{CC} = 3 V		-24				
		V _{CC} = 4.5 V		-32				
		V _{CC} = 1.65 V		4				
		V _{CC} = 2.3 V		8				
I _{OL}	Low-level output current			16	mA			
		$V_{CC} = 3 V$		24				
		V _{CC} = 4.5 V		32				
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20				
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V			
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5				
_		DSBGA package	-40	85	°C			
T_A	Operating free-air temperature	All other packages	-40	125	°C			

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

6.4 Thermal Information

				SN741	VC1G32			
	TUEDMAL METRIC(1)							⊢
	THERMAL METRIC ⁽¹⁾	DBV	DCK	DRL	DRY	YZP	DPW	UNIT
		5 PINS	5 PINS	5 PINS	6 PINS	5 PINS	4 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	229	278	243	439	130	340	
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance	164	93	78	277	54	215	
$R_{\theta JB}$	Junction-to-board thermal resistance	62	65	78	271	51	294	°C/W
ψ_{JT}	Junction-to-top characterization parameter	44	2	10	84	1	41	*C/VV
ψ_{JB}	Junction-to-board characterization parameter	62	64	77	271	50	294	
$R_{\theta JCbot}$	Junction-to-case (bottom) thermal resistance	-	_	-	_	_	250	

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report (SPRA953).



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	-40°0	C to 85°C		to 125°C		UNIT		
			MIN	TYP ⁽¹⁾ MAX	MIN	TYP	MAX			
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1		V _{CC} - 0.1					
	I _{OH} = -4 mA	1.65 V	1.2		1.2					
V	I _{OH} = -8 mA	2.3 V	1.9		1.9			V		
V _{OH}	I _{OH} = -16 mA	3 V	2.4		2.4			V		
	I _{OH} = -24 mA	3 V	2.3		2.3					
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		3.8					
	I _{OL} = 100 μA	1.65 V to 5.5 V		0.1			0.1			
	I _{OL} = 4 mA	1.65 V		0.45			0.45			
V	I _{OL} = 8 mA	2.3 V		0.3			0.4	V		
V _{OL}	I _{OL} = 16 mA	3 V		0.4			0.5	V		
	I _{OL} = 24 mA	3 V		0.55			0.65			
	I _{OL} = 32 mA	4.5 V		0.55			0.65			
I _I A or B inputs	V _I = 5.5 V or GND	0 to 5.5 V		±5			±5	μΑ		
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±10			±25	μΑ		
Icc	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V		10			10	μΑ		
ΔI _{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V	500			500	μΑ			
C _i	V _I = V _{CC} or GND	3.3 V		4		4		pF		

⁽¹⁾ All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

6.6 Switching Characteristics, $C_L = 15 pF$

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 3)

Ī							-40°C t	o 85°C				
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = ± 0.2		V _{CC} = 3 ± 0.3		V _{CC} = ± 0.9		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	t _{pd}	A or B	Y	1.9	7.2	0.8	4.4	0.9	3.6	0.8	3.4	ns

6.7 Switching Characteristics, 1.8 V and 2.5V

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ or 50 pF (unless otherwise noted)⁽¹⁾ (see Figure 4)

		FPOM	TO	-40°C to 85°C		-40°C to 125°C RECOMMENDED		-40°C to 85°C		-40°C to 125°C RECOMMENDED		
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1. ± 0.15		V _{CC} = 1 ± 0.15		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.5 V ± 0.2 V	UNIT	
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
ſ	t_{pd}	A or B	Υ	2.8	8	2.8	9	1.2	5.5	1.2	6	ns

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

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6.8 Switching Characteristics, 3.3 V and 5 V

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ or 50 pF (unless otherwise noted)⁽¹⁾ (see Figure 4)

	PARAMETER			−40°C to	-40°C to 85°C		-40°C to 125°C RECOMMENDED		85°C	-40°C to RECOMME		
		FROM (INPUT)	TO (OUTPUT)	V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		V _{CC} = 5 V ± 0.5 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	t _{pd}	A or B	Υ	1.1	4.5	1	4	1	4	1	4.5	ns

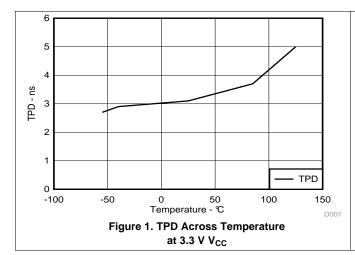
⁽¹⁾ On products compliant to MIL-PRF-38535, this parameter is not production tested

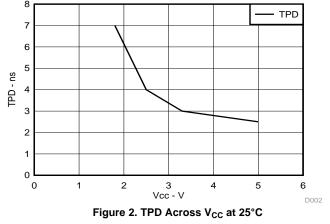
6.9 Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT	
	FARAMETER	CONDITIONS	TYP	TYP	TYP	TYP	UNII	
С	pd Power dissipation capacitance	f = 10 MHz	20	20	21	22	pF	

6.10 Typical Characteristics



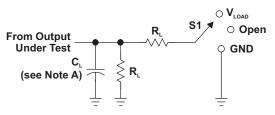


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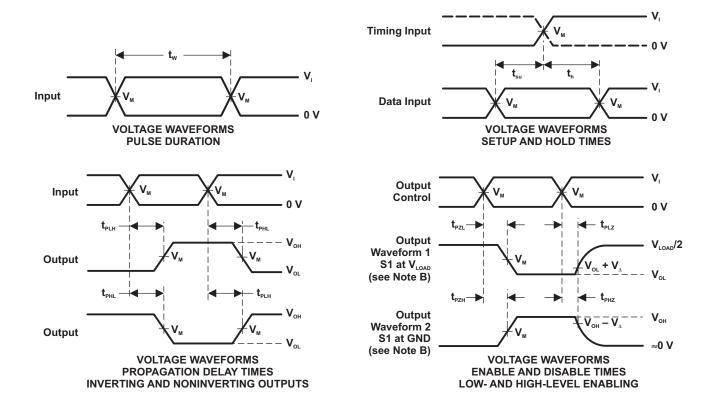
7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

		30	

.,	INI	PUTS		.,			.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _∟	R _⊾	V _A
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$2.5 \text{ V} \pm 0.2 \text{ V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$3.3 \text{ V} \pm 0.3 \text{ V}$	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

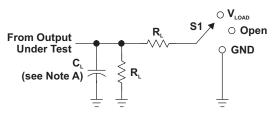
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{\circ} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $t_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

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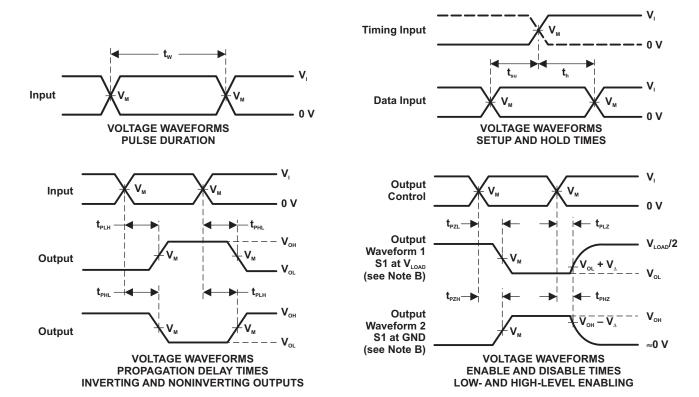
Parameter Measurement Information (continued)



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

,,	INI	PUTS		V			.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _⊾	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
$2.5~\textrm{V}~\pm~0.2~\textrm{V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
$3.3~V~\pm~0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \,\Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

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8 Detailed Description

8.1 Overview

The SN74LVC1G32 device contains one 2-input positive OR gate device and performs the Boolean function $Y = A + B \text{ or } Y = \overline{A \bullet B}$. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The DPW package technology is a major breakthrough in IC packaging. Its tiny 0.64 mm square footprint saves significant board space over other package options while still retaining the traditional manufacturing friendly lead pitch of 0.5 mm.

8.2 Functional Block Diagram



8.3 Feature Description

- Wide operating voltage range.
 - Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- I_{off} feature allows voltages on the inputs and outputs, when V_{CC} is 0 V.

8.4 Device Functional Modes

Function Table

INP	UTS	OUTPUT					
Α	В	Y					
Н	X	Н					
X	Н	Н					
L	L	L					

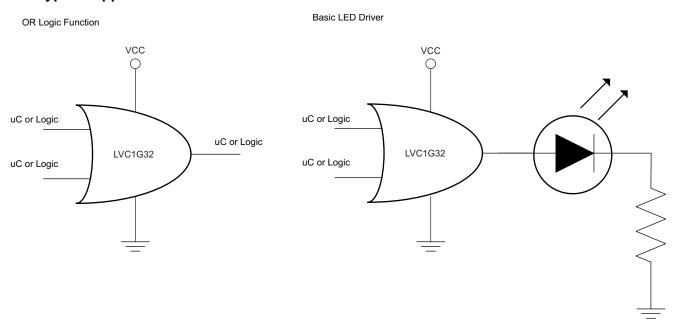


9 Application and Implementation

9.1 Application Information

The SN74LVC1G32 device is a high drive CMOS device that can be used for implementing OR logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing translation down to $V_{\rm CC}$.

9.2 Typical Application



9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - Rise time and fall time specs. See (Δt/ΔV) in the Recommended Operating Conditions table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Recommended Operating
 Conditions table at any valid V_{CC}.

2. Recommend Output Conditions:

- Load currents should not exceed (I_O max) per output and should not exceed total current (continuous current through V_{CC} or GND) for the part. These limits are located in the *Absolute Maximum Ratings* table.
- Outputs should not be pulled above V_{CC}.

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Typical Application (continued)

9.2.3 Application Curves

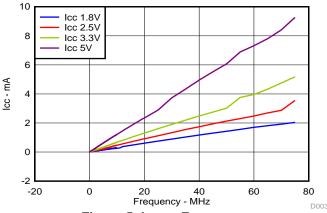


Figure 5. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the *Recommended Operating Conditions* table.

Each VCC pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF capacitor is recommended. If there are multiple VCC pins, then a 0.01-μF or 0.022-μF capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. A 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float.

In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used, or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Layout Example are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or VCC, whichever make more sense or is more convenient.

11.2 Layout Example





12 Device and Documentation Support

12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





www.ti.com 1-Jun-2022

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G32DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C325, C32F, C32J, C32K, C32R) (C32H, C32P, C32S)	Samples
SN74LVC1G32DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32F	Samples
SN74LVC1G32DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32F	Samples
SN74LVC1G32DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C325, C32F, C32J, C32K, C32R) (C32H, C32P, C32S)	Samples
SN74LVC1G32DBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32F	Samples
SN74LVC1G32DCK3	ACTIVE	SC70	DCK	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	(CGF, CGZ)	Samples
SN74LVC1G32DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CG5, CGF, CGJ, CG K, CGR) (CGH, CGP, CGS)	Samples
SN74LVC1G32DCKRE4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CG5 CGS	Samples
SN74LVC1G32DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CG5 CGS	Samples
SN74LVC1G32DCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CG5, CGF, CGJ, CG K, CGR) (CGH, CGP, CGS)	Samples
SN74LVC1G32DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CG5 CGS	Samples
SN74LVC1G32DPWR	ACTIVE	X2SON	DPW	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	N4	Samples
SN74LVC1G32DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CG7, CGR)	Samples
SN74LVC1G32DRLRG4	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CG7, CGR)	Samples
SN74LVC1G32DRY2	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CG	Samples



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Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G32DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CG	Samples
SN74LVC1G32DSF2	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CG	Samples
SN74LVC1G32DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	CG	Samples
SN74LVC1G32YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(CG, CG7)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G32:

Automotive: SN74LVC1G32-Q1

● Enhanced Product : SN74LVC1G32-EP

NOTE: Qualified Version Definitions:

- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications



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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G32DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G32DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G32DBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G32DBVTG4	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G32DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G32DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G32DCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G32DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G32DCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G32DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G32DPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q3
SN74LVC1G32DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G32DRY2	SON	DRY	6	5000	180.0	9.5	1.6	1.15	0.75	4.0	8.0	Q3
SN74LVC1G32DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G32DSF2	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q3
SN74LVC1G32DSFR	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.63	4.0	8.0	Q2



PACKAGE MATERIALS INFORMATION

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	Device		Package Drawing	l .	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ĺ	SN74LVC1G32DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
ĺ	SN74LVC1G32YZPR	DSBGA	YZP	5	3000	180.0	8.4	1.02	1.52	0.63	4.0	8.0	Q1



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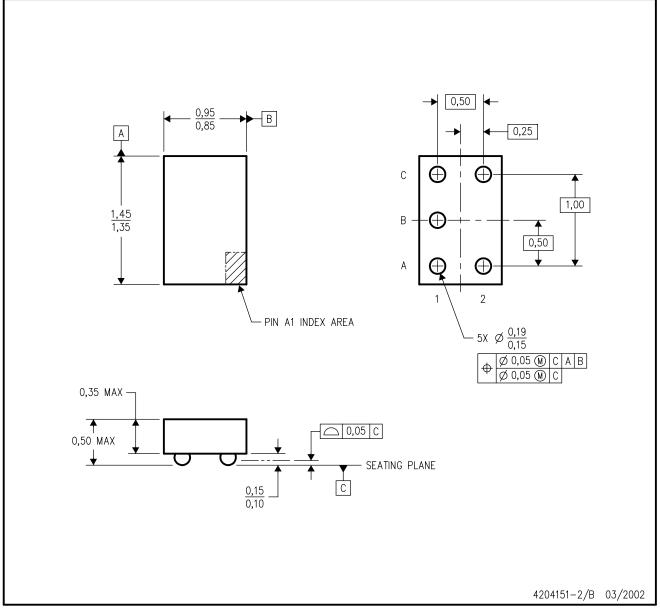


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G32DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LVC1G32DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G32DBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
SN74LVC1G32DBVTG4	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G32DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G32DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G32DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G32DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G32DCKT	SC70	DCK	5	250	202.0	201.0	28.0
SN74LVC1G32DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G32DPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
SN74LVC1G32DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G32DRY2	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G32DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G32DSF2	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC1G32DSFR	SON	DSF	6	5000	202.0	201.0	28.0
SN74LVC1G32DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC1G32YZPR	DSBGA	YZP	5	3000	182.0	182.0	20.0

YZA (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoFree $^{\text{TM}}$ package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is lead-free. Refer to the 5 YEA package (drawing 4203167) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4211218-3/D







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.





NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).





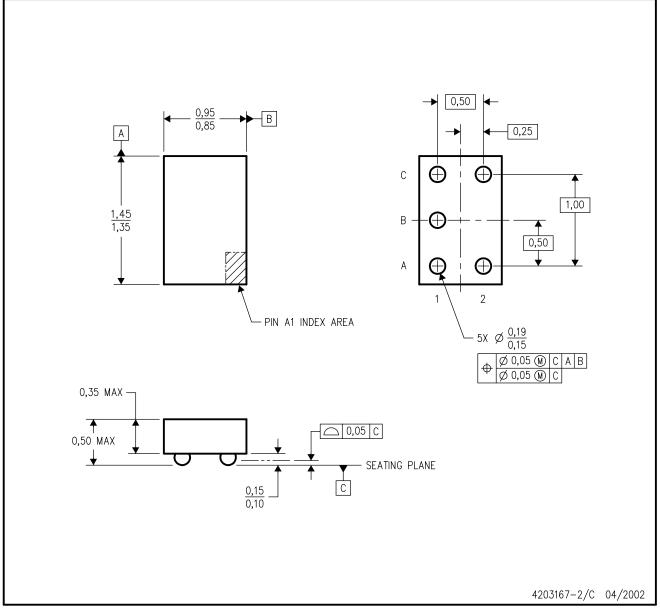
NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



YEA (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is tin-lead (SnPb). Refer to the 5 YZA package (drawing 4204151) for lead-free.

NanoStar is a trademark of Texas Instruments.





DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 7. Board assembly site may have different recommendations for stencil design.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





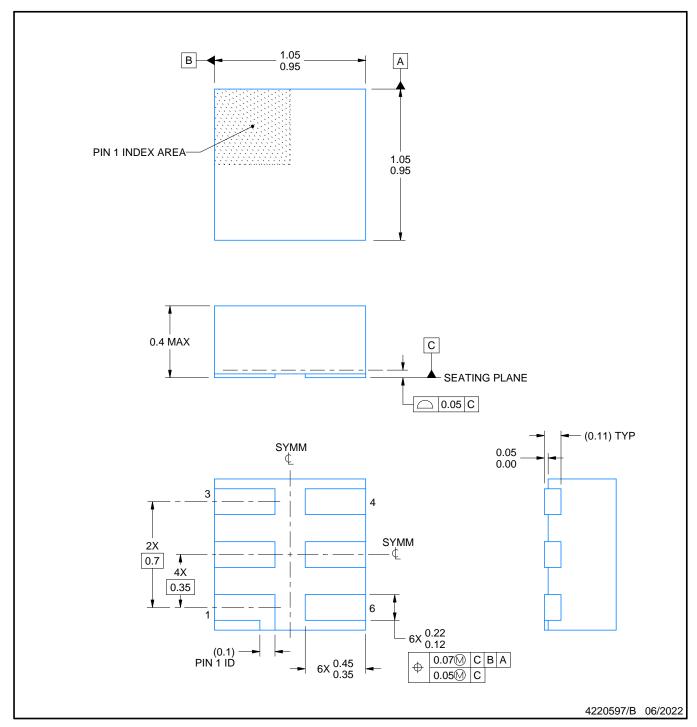
NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



PLASTIC SMALL OUTLINE - NO LEAD



4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)

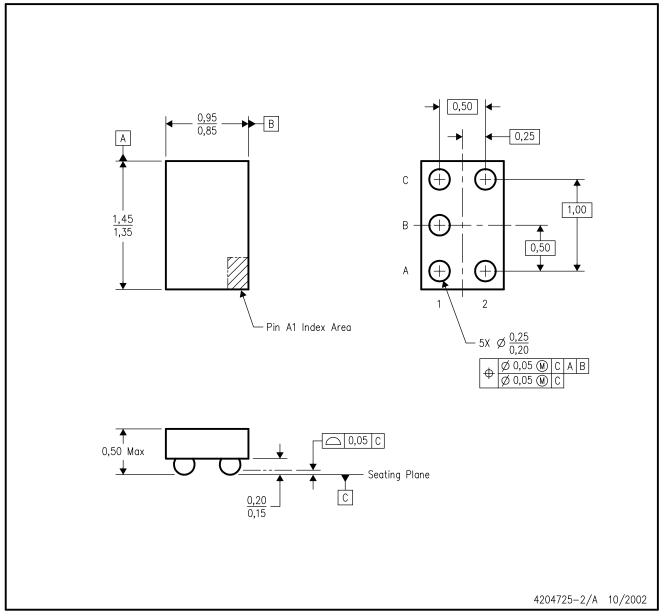


^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

YEP (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

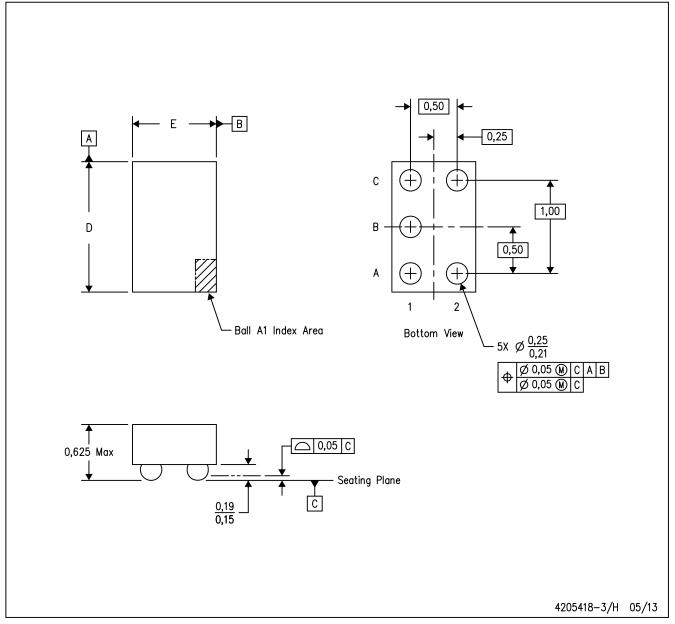
- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. This package is tin-lead (SnPb). Refer to the 5 YZP package (drawing 4204741) for lead-free.

NanoStar is a trademark of Texas Instruments.



YZT (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.



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